
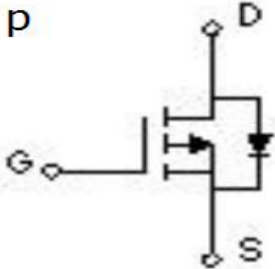
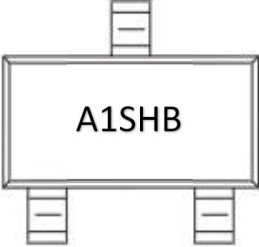
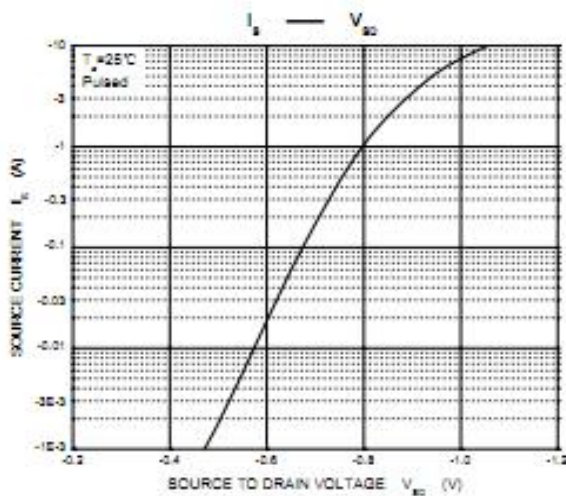
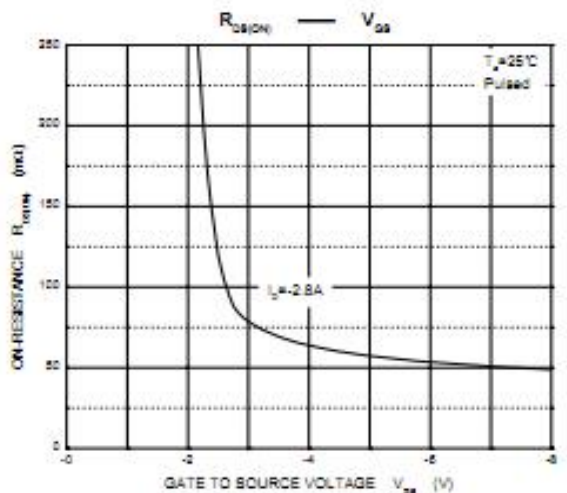
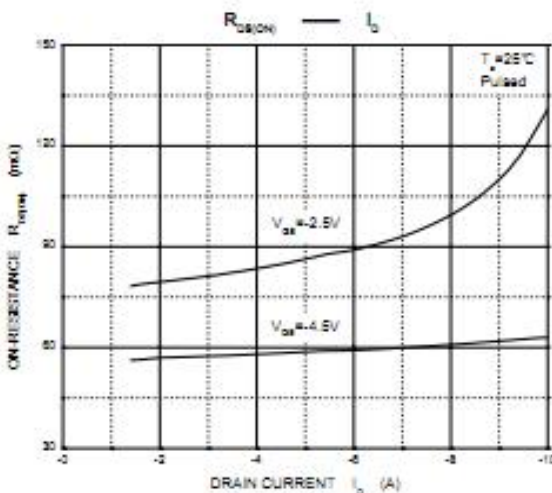
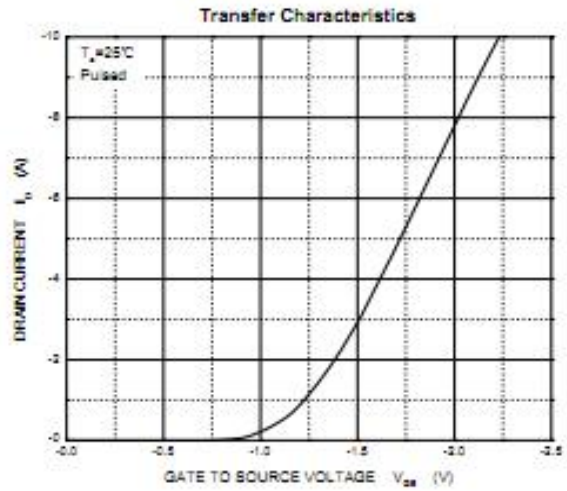
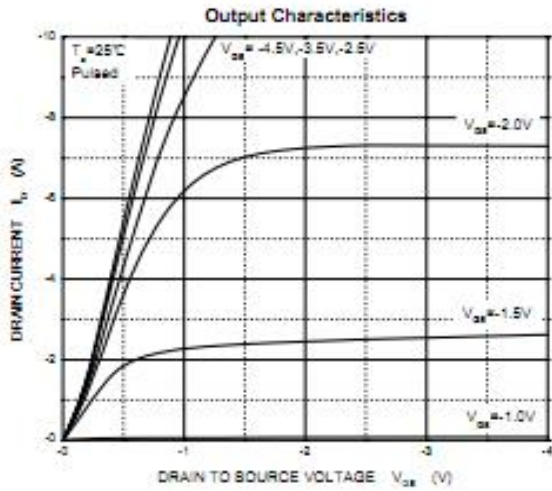


P-Channel 20-V(D-S) MOSFET		SOT-23 Plastic-Encapsulate MOSFETS	
<p style="text-align: center;"><u>SOT-23</u></p>  <p>1.GATE 2.SOURCE 3.DRAIN</p> <p style="text-align: center;">Equivalent Circuit</p> 		<p>Features</p> <ul style="list-style-type: none"> ※ TrenchFET Power MOSFET <p>Application</p> <ul style="list-style-type: none"> ※ Load Switch for Portable Devices ※ DC/DC Converter <p>MARKING</p> 	
<p>Maximum ratings (Ta=25°C unless otherwise noted)</p>			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	VGS	±8	
Continuous Drain Current	ID	-2.3	A
Pulsed Diode Current	IDM	-10	
Continuous Source-Drain Current(Diode Conduction)	IS	-0.72	
Power Dissipation	PD	0.35	W
Thermal Resistance from Junction to Ambient (t≤5s)	R θ JA	357	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C

MOSFET ELECTRICAL CHARACTERISTICS						
Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250µA	-20			V
Gate-source threshold voltage	VGS(th)	VDS = VGS, ID = -250µA	-0.4	-0.75	-1	V
Gate-source leakage	IGSS	VDS = 0V, VGS = ±8V		±1.3	±100	nA
Zero gate voltage drain current	IDSS	VDS = -20V, VGS = 0V			-1	µA
Drain-source on-state resistancea	RDS(on)	VGS = -4.5V, ID = -2.8A		130	185	mΩ
		VGS = -2.5V, ID = -2A		175	280	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -2.8A		4		S
Diode forward voltage	VSD	IS = -0.8A, VGS = 0V		-0.8	-1.3	V
Dynamic						
Input capacitance	Ciss	VDS = -10V, VGS = 0V, f = 1MHz		405		pF
Output capacitance	Coss			75		pF
Reverse transfer capacitanceb	Crss			55		pF
Total gate charge	Qg	VDS = -10V, VGS = -4.5V, ID = -3A		5.5	10	nC
		VDS = -10V, VGS = -2.5V, ID = -3A		3.3	6	nC
Gate-source charge	Qgs	VDS = -10V, VGS = -2.5V, ID = -3A		0.7		nC
Gate-drain charge	Qgd			1.3		nC
Gate resistance	Rg	f = 1MHz		6.0		Ω
Switchingb						
Turn-on delay time	td(on)	VDD = -10V RL = 10Ω, ID ≈ -1A, VGEN = -4.5V, Rg = 1Ω		11	20	ns
Rise time	tr			35	60	ns
Turn-off delay time	td(off)			30	50	ns
Fall time	tf			10	20	ns
Drain-source body diode characteristics						
Continuous Source-Drain Diode Current	IS	Tc = 25°C			-1.3	A
Pulsed Diode forward Current	ISM				-10	A
Note :						
1. Repetitive Rating : Pulse width limited by maximum junction temperature.						
2. Surface Mounted on FR4 Board, t < 5 sec.						
3. Pulse Test : Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.						
4. Guaranteed by design, not subject to production testing.						

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)